



# B1D08065KF

650V ▲ 8A ▲ SiC SCHOTTKY DIODE

SILICON CARBIDE SiC SCHOTTKY DIODE ▲ THT type

Excellent surge capability

Easy paralleling due to positive  $V_F$  temperature coefficient

Temperature independent switching



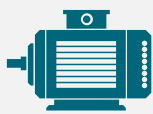




Low forward voltage

TO-220F-2L package ▲ Electrical insulated mounting tab

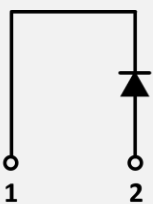
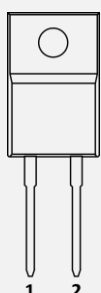
## SPECIFICATION

Item ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)		Characteristics
Operating Temperature Range	$T_J$	$-55^\circ\text{C}$ to $+175^\circ\text{C}$
Storage Temperature Range	$T_S$	$-55^\circ\text{C}$ to $+175^\circ\text{C}$
Repetitive Peak Reverse Voltage	$V_{RRM}$	650V
Continuous Forward Current at $T_C = 130^\circ\text{C}$	$I_F$	8A
Total Capacitive Charge ( $T_J = 25^\circ\text{C}$ )	$Q_C$	24nC
Capacitance Stored Energy ( $V_R = 400\text{V}$ )	$E_C$	6μJ
Diode Forward Voltage ( $T_J = 175^\circ\text{C}$ , $I_F = 8\text{A}$ )	$V_F$	1.69V
Power Dissipation	$P_{TOT}$	48W

## APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
						

## PIN DESCRIPTION

Circuit Diagram	Outline - Front View	Pin No.	Description
		1 2	Cathode Anode

## ABSOLUT MAXIMUM RATINGS ▲ $T_C = 25^\circ\text{C}$ , unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		$V_{RRM}$	650	V
Non-Repetitive Peak Reverse Voltage		$V_{RSM}$	650	V
Continuous Forward Current	$T_C = 25^\circ\text{C}$	$I_F$	17	A
Continuous Forward Current	$T_C = 130^\circ\text{C}$	$I_F$	8	A
Non-Repetitive Forward Surge Current	$T_C = 25^\circ\text{C}$ , $t_p = 10\text{ms}$ , Half Sine Wave	$I_{FSM}$	64	A
$I^2t$ Value	$T_C = 25^\circ\text{C}$ , $t_p = 10\text{ms}$	$\int i^2 dt$	20.48	$\text{A}^2\text{s}$
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_{TOT}$	48	W
Power Dissipation	$T_C = 110^\circ\text{C}$	$P_{TOT}$	20	W
Operating Junction Temperature		$T_J$	-55 to +175	$^\circ\text{C}$
Storage Temperature Range		$T_{STG}$	-55 to +175	$^\circ\text{C}$
TO-220 Mounting Torque	M3 Screw		0.7	Nm

## ELECTRICAL CHARACTERISTICS

Item	Condition	Symbol	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
DC Blocking Voltage	$T_J = 25^\circ\text{C}$	$V_{DC}$	650			V
Diode Forward Voltage	$I_F = 8\text{A}$ , $T_J = 25^\circ\text{C}$	$V_F$		1.40	1.60	V
Diode Forward Voltage	$I_F = 8\text{A}$ , $T_J = 175^\circ\text{C}$	$V_F$		1.69	2.00	V
Reverse Current	$V_R = 650\text{V}$ , $T_J = 25^\circ\text{C}$	$I_R$		1	70	$\mu\text{A}$
Reverse Current	$V_R = 650\text{V}$ , $T_J = 175^\circ\text{C}$	$I_R$		10	200	$\mu\text{A}$

Item	Condition	Symbol	Min.	Typ.	Max.	Unit
<b>Dynamic Characteristics</b>						
Total Capacitive Charge	$V_R = 400\text{V}$ , $T_J = 25^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V) dV$	$Q_C$		24		nC
Total Capacitance	$V_R = 1\text{V}$ , $f = 1\text{MHz}$ , $T_J = 25^\circ\text{C}$	$C$		365		pF
Total Capacitance	$V_R = 300\text{V}$ , $f = 1\text{MHz}$ , $T_J = 25^\circ\text{C}$	$C$		41.1		pF
Total Capacitance	$V_R = 600\text{V}$ , $f = 1\text{MHz}$ , $T_J = 25^\circ\text{C}$	$C$		40.7		pF
Capacitance Stored Energy	$V_R = 400\text{V}$ , $T_J = 25^\circ\text{C}$	$E_C$		6		$\mu\text{J}$

## THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		3.1		K/W

## REFERENCE DATA ▲ TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics  $I_F$  vs.  $V_F$

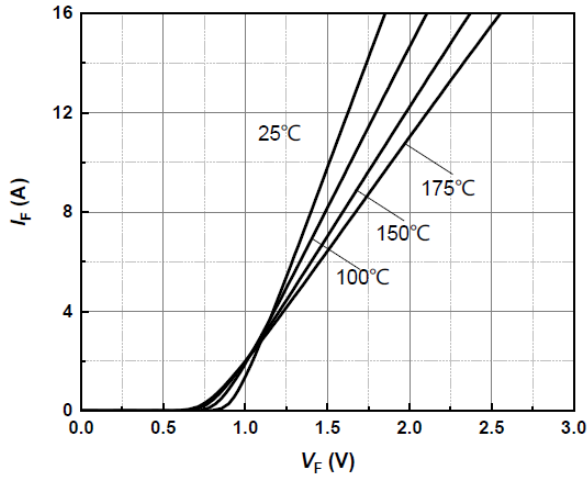


Fig. 2 • Typical Reverse Current  $I_R$  as function of Reverse Voltage  $V_R$

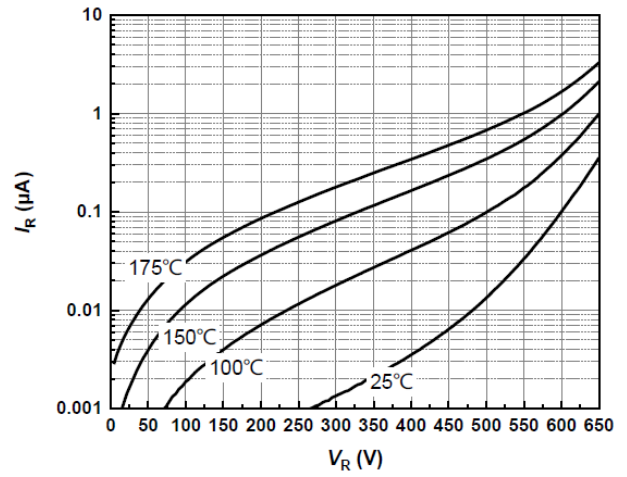


Fig. 3 • Diode Forward Current  $I_F$  as function of Case Temperature  $T_C$  ( $D = \text{Duty Cycle}$ )

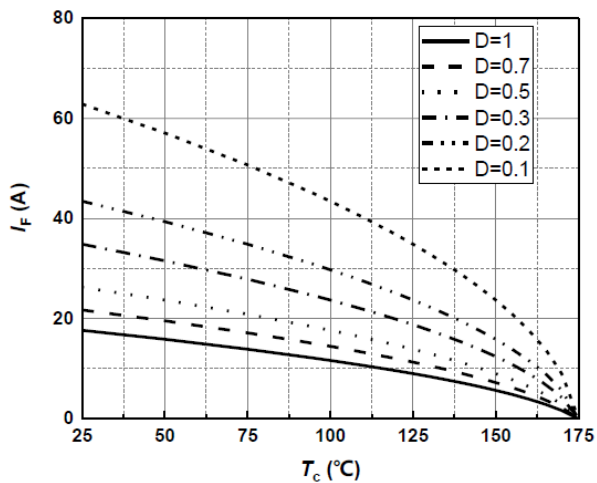


Fig. 4 • Typical Capacitance  $C$  as function of Reverse Voltage  $V_R$ ,  $C = f(V_R)$ ,  $T_J = 25^\circ\text{C}$ ,  $f = 1\text{MHz}$

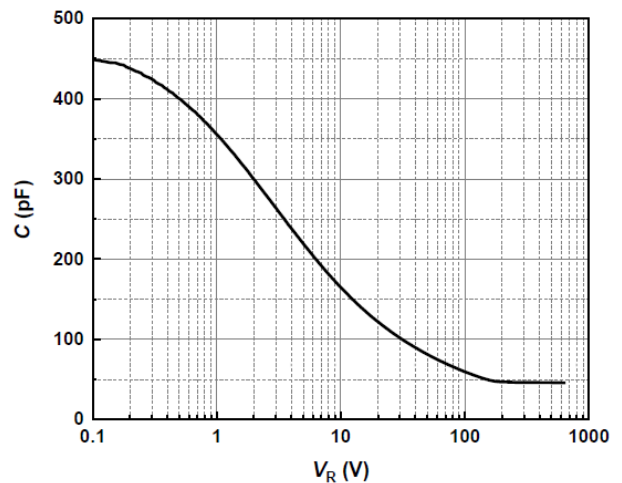


Fig. 5 • Typical Reverse Charge  $Q_C$  as function of Reverse Voltage  $V_R$

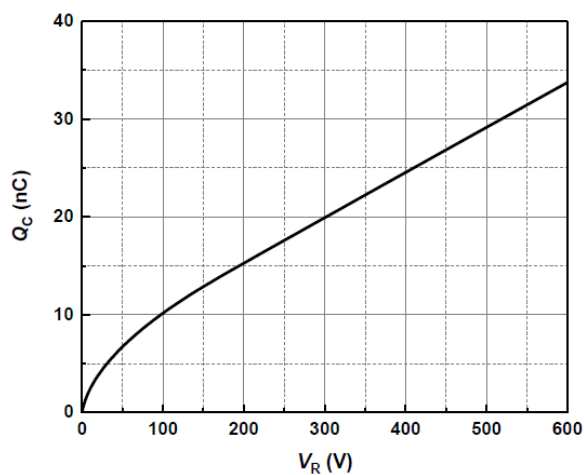
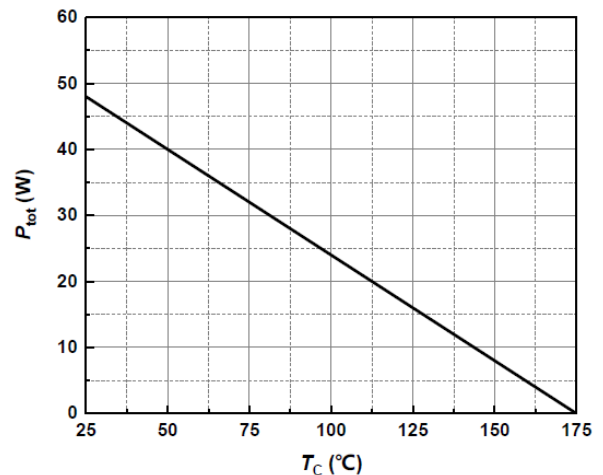


Fig. 6 • Power Dissipation  $P_{TOT}$  as function of Case Temperature  $T_C$



## REFERENCE DATA ▲ TYPICAL PERFORMANCE

Fig. 7 • Capacitance Stored Energy

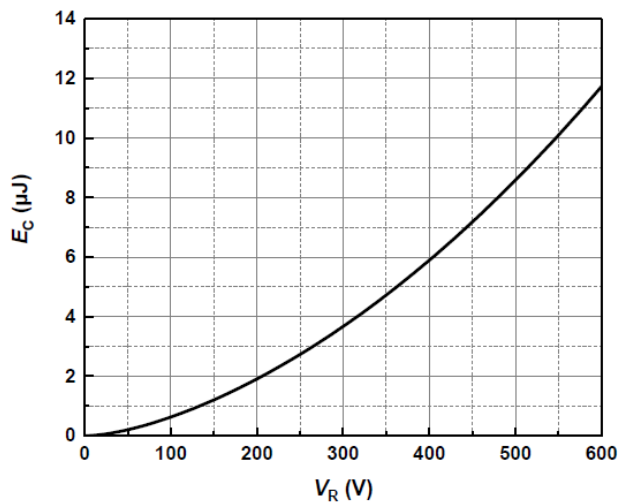
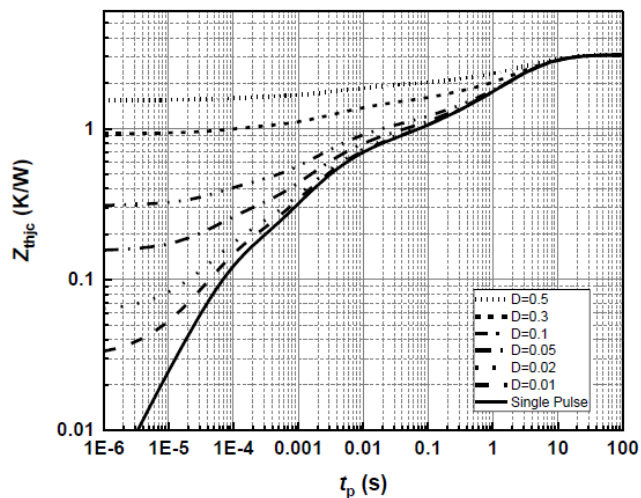
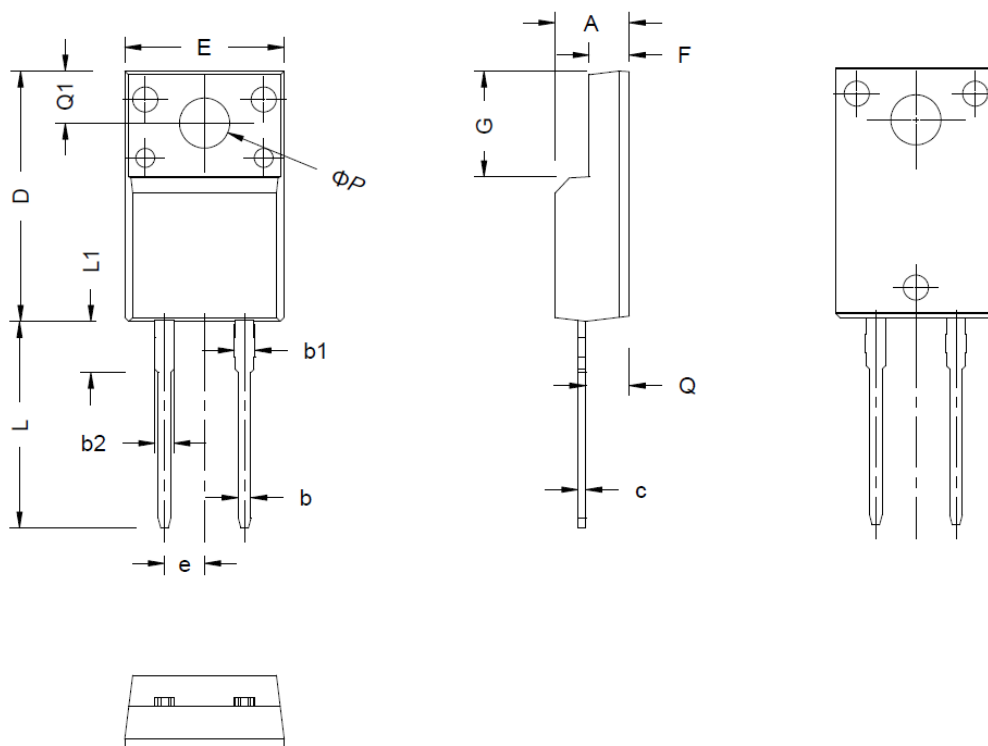


Fig. 8 • Maximum Transient Thermal Impedance,  $Z_{thjc} = f(t)$ , Parameter:  $D = t/T$



## PACKAGE OUTLINE



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
c	0.45	0.50	0.63
D	15.80	15.87	15.97
D	15.15	15.45	15.75
e	2.54 BSC		
E	10.00	10.10	10.30

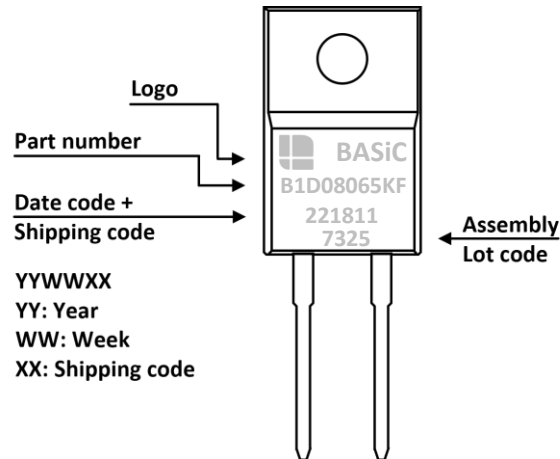
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L	12.70	-	13.70
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
ØP	2.08	3.18	3.28

TO-220F-2L package ▲ Epoxy meets UL94-V0

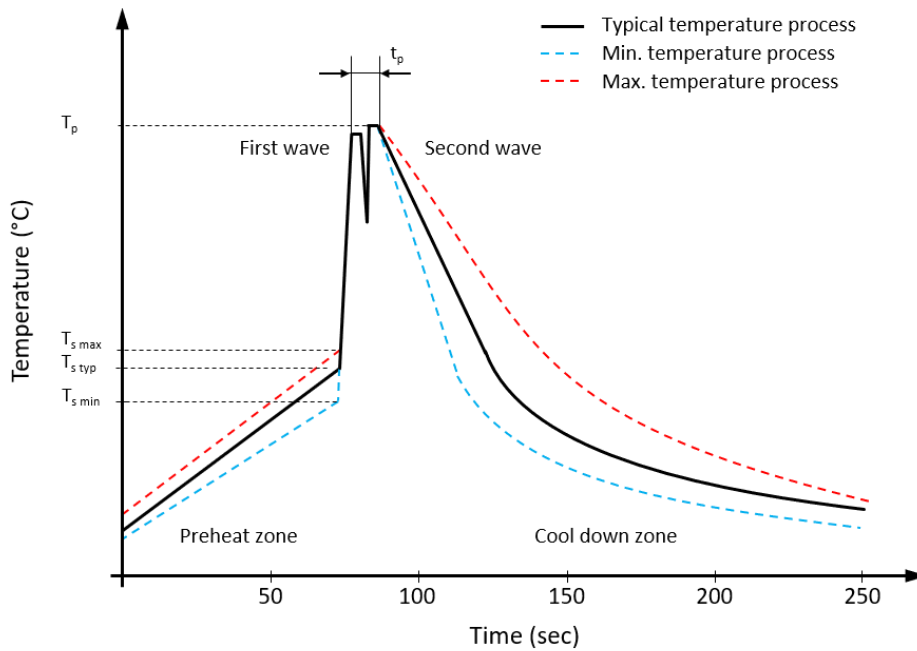
## ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B1D08065KF	TO-220F-2L	Tube	50pcs	500pcs	5,000pcs

## PART MARKING



## RECOMMENDED WAVE SOLDERING PROFILE ▲ THT PACKAGE



### Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	$T_{s \min}$	100 °C	100 °C
Preheat temperature typical	$T_{s \text{ typ}}$	120 °C	120 °C
Preheat temperature max.	$T_{s \max}$	130 °C	130 °C
Preheat time $t_s$ from $T_{s \min}$ to $T_{s \max}$	$t_s$	70 seconds	70 seconds
Peak temperature	$T_p$	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	$t_p$	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down rate min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes

## REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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